

Inventor(s): Bayer et al.
Atty. Ref. 706652US2

Inventor(s): Bayer et al.
Atty. Ref. 706652US2

1/4

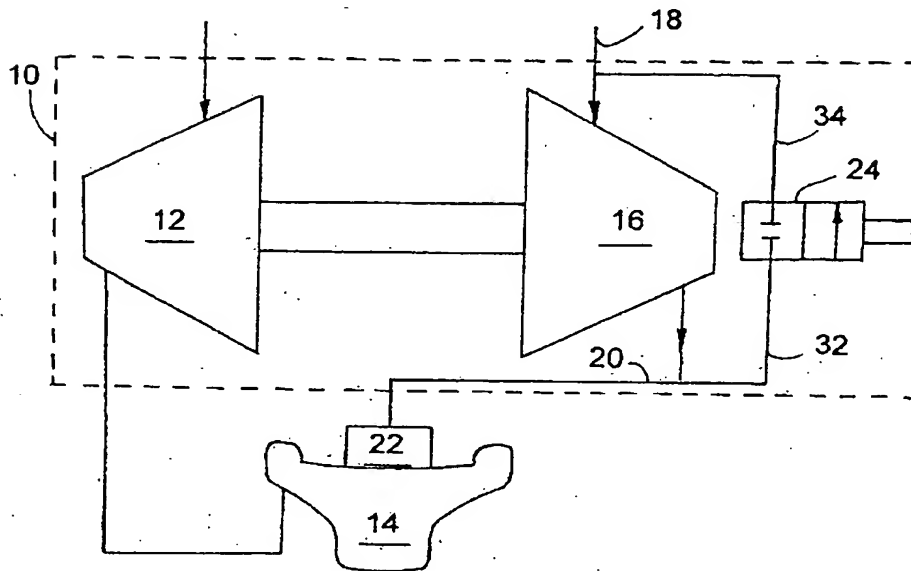


FIG. 1
PRIOR ART

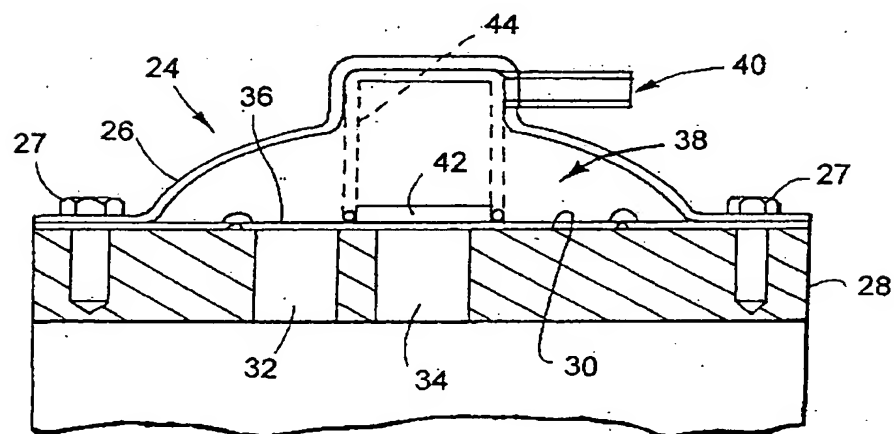


FIG. 3
PRIOR ART

**Title: EXTERNAL BLOW OFF CONVERSION
OF COMPRESSOR RECIRCULATION VALVE**

**Inventor(s): Bayer et al.
Atty. Ref. 706652US2**

2/4

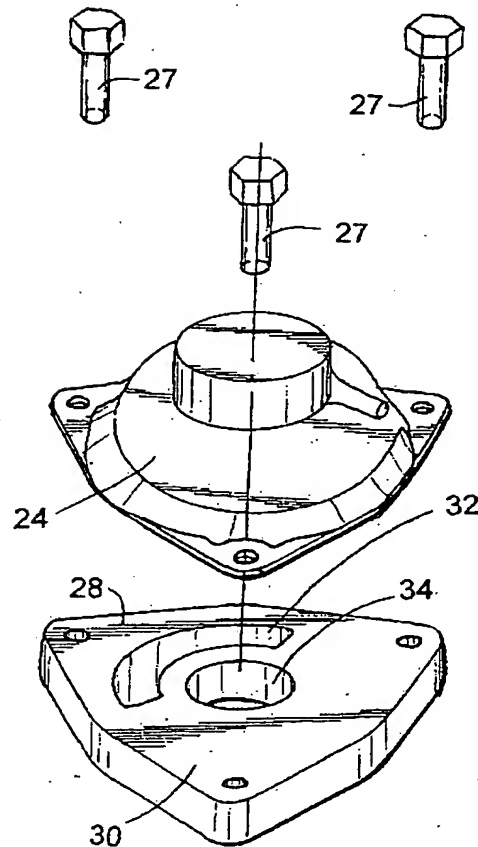


FIG. 2
PRIOR ART

**Title: EXTERNAL BLOW OFF CONVERSION
OF COMPRESSOR RECIRCULATION VALVE**

**Inventor(s): Bayer et al.
Atty. Ref. 706652US2**

3/4

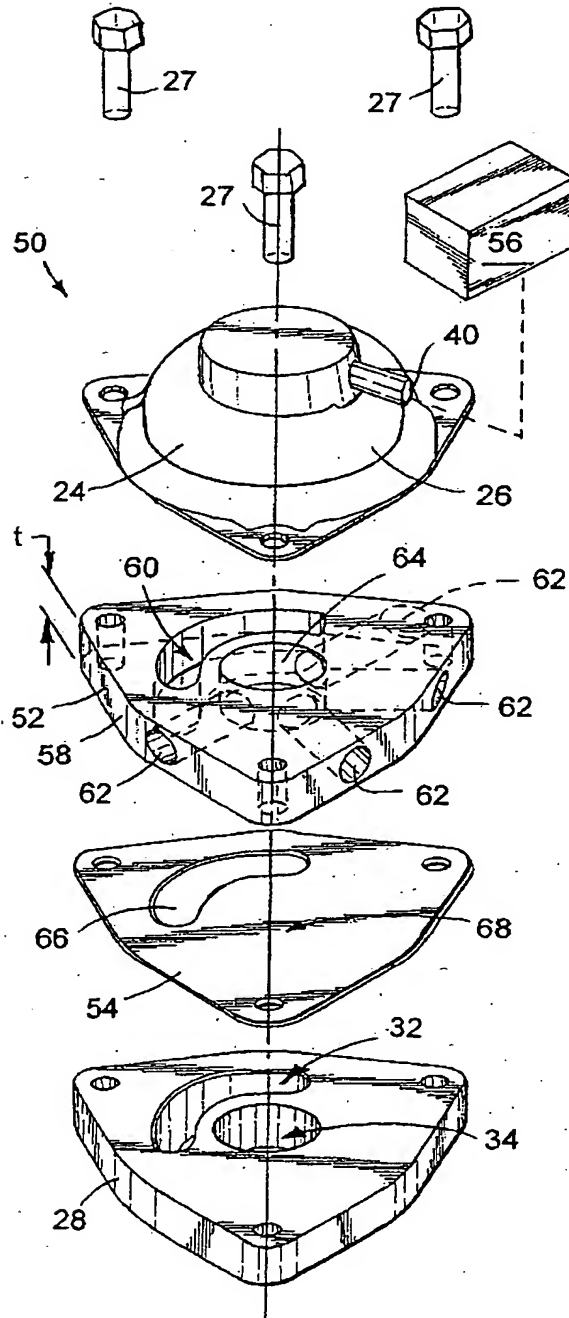


FIG. 4

Inventor(s): Bayer et al.
Atty. Ref. 706652US2

This cross-sectional view shows a semiconductor device with a central gate structure. The device consists of a substrate (28) with a top layer (62) and a bottom layer (60). A central gate structure (42) is formed on the top layer, with a gate electrode (40) on top. The gate structure is surrounded by a gate oxide layer (36). The device is further defined by a top layer (24) and a bottom layer (26). The central gate structure is connected to a central electrode (44) via a contact (42). The device is further defined by a top layer (24) and a bottom layer (26). The central gate structure is connected to a central electrode (44) via a contact (42). The device is further defined by a top layer (24) and a bottom layer (26). The central gate structure is connected to a central electrode (44) via a contact (42).

FIG. 6